

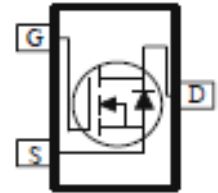
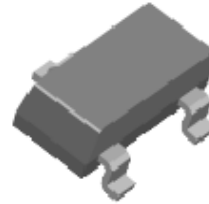
Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
150	1200 @ $V_{GS} = 10V$	0.9
	1300 @ $V_{GS} = 4.5V$	0.8



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	0.9	A
	$T_A=70^\circ\text{C}$		0.7	
Pulsed Drain Current ^b		I_{DM}	10	
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	A
Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	1.3	W
	$T_A=70^\circ\text{C}$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
	Steady State		166	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

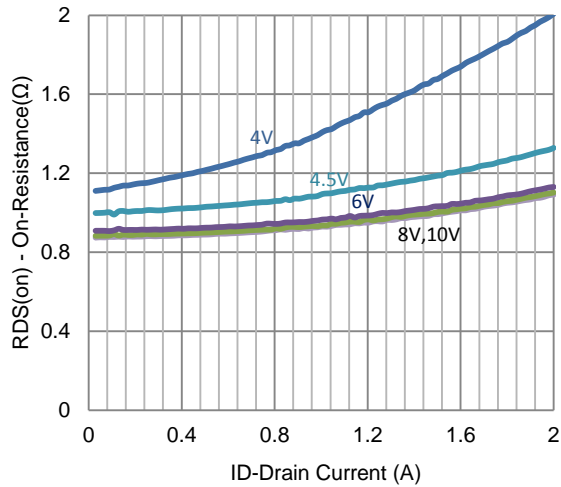
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 120 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	5			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 0.9 A$			1200	m Ω
		$V_{GS} = 4.5 V, I_D = 0.8 A$			1300	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 0.9 A$		15		S
Diode Forward Voltage	V_{SD}	$I_S = 0.9 A, V_{GS} = 0 V$		0.82		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 75 V, V_{GS} = 4.5 V,$ $I_D = 0.9 A$		3		nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 75 V, R_L = 83.4 \Omega,$ $I_D = 0.9 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		4		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			19		
Fall Time	t_f			6		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		179		pF
Output Capacitance	C_{oss}			14		
Reverse Transfer Capacitance	C_{rss}			12		

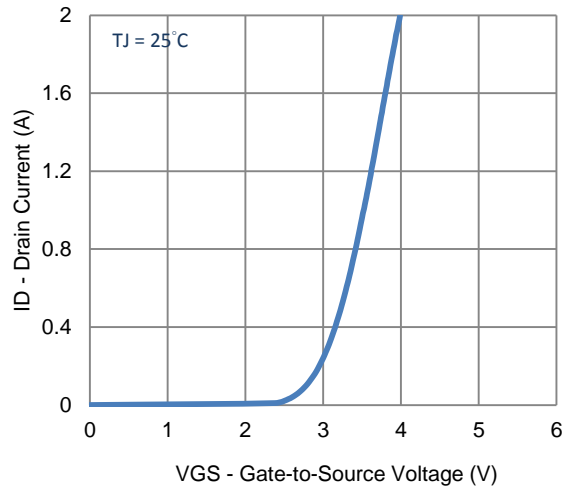
Notes

- Pulse test: PW \leq 300us duty cycle \leq 2%.
- Guaranteed by design, not subject to production testing.

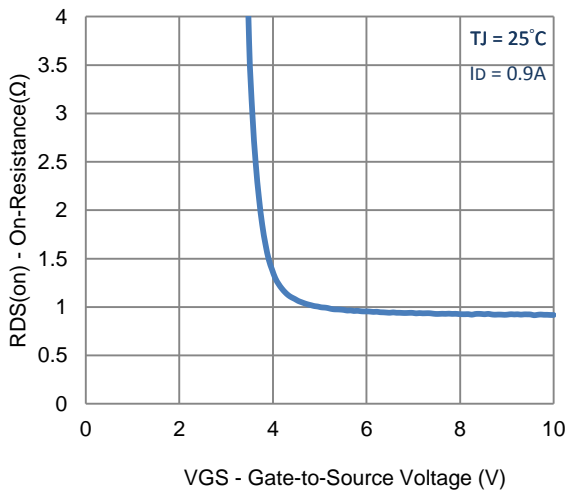
Typical Electrical Characteristics



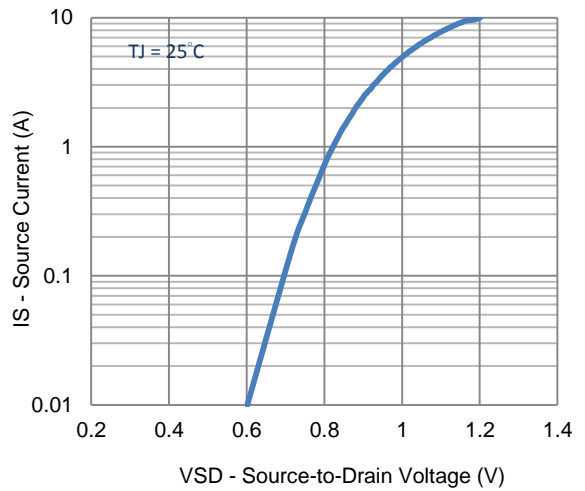
1. On-Resistance vs. Drain Current



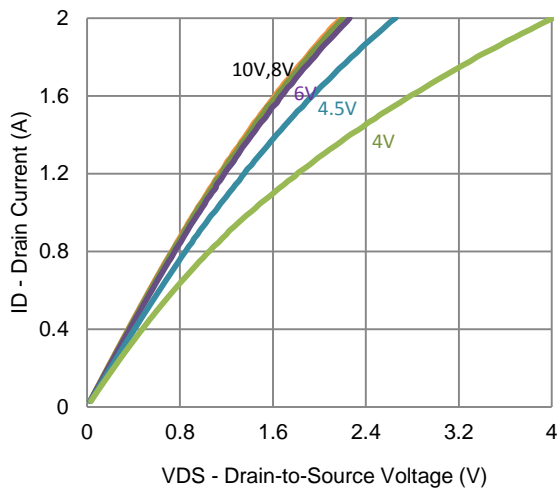
2. Transfer Characteristics



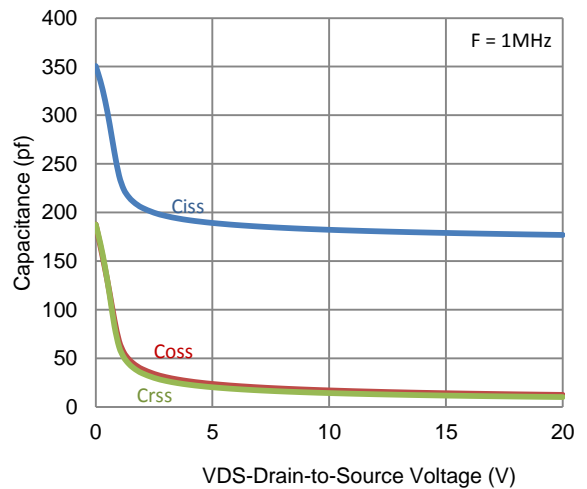
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

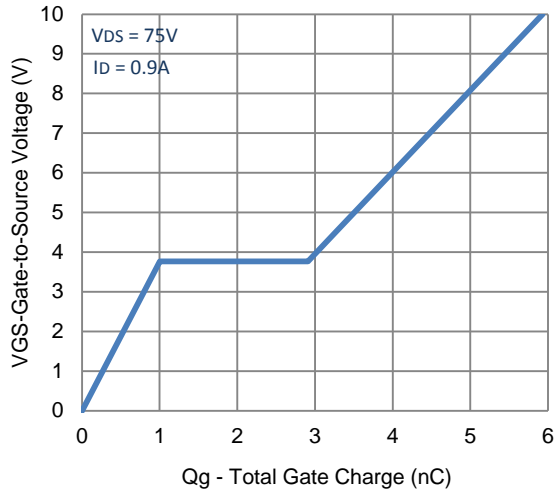


5. Output Characteristics

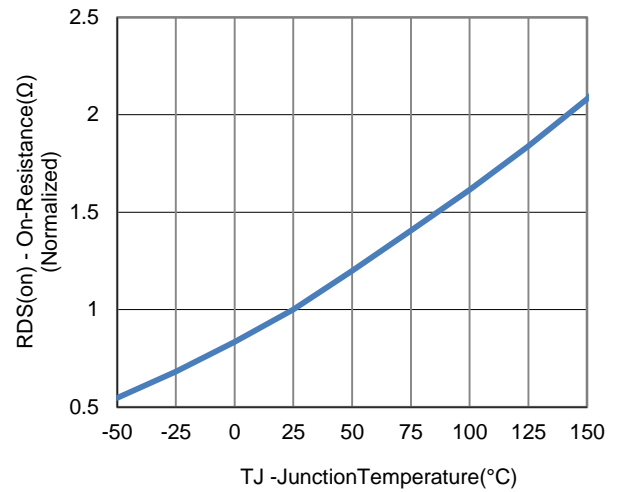


6. Capacitance

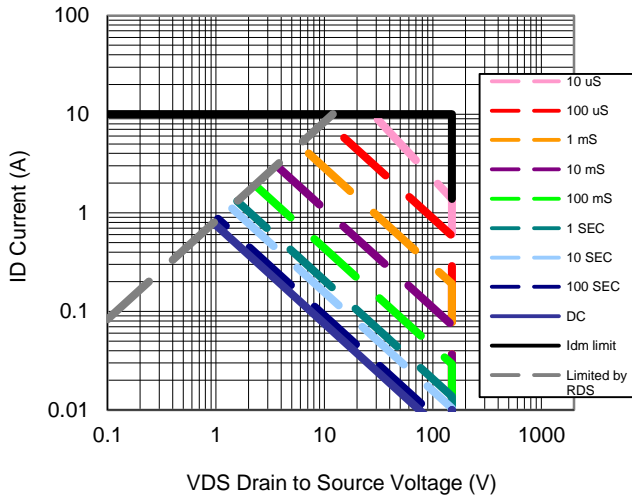
Typical Electrical Characteristics



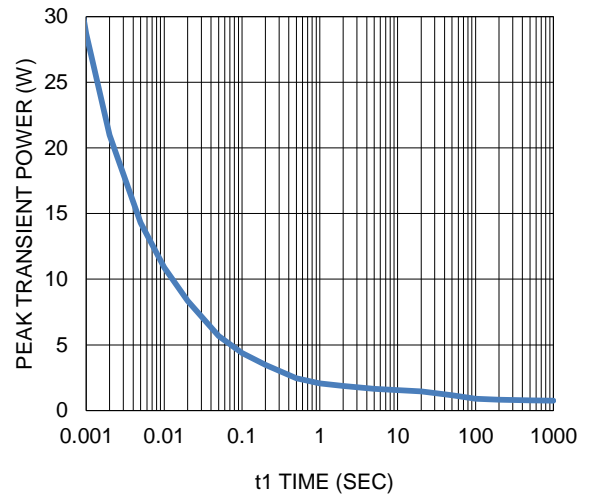
7. Gate Charge



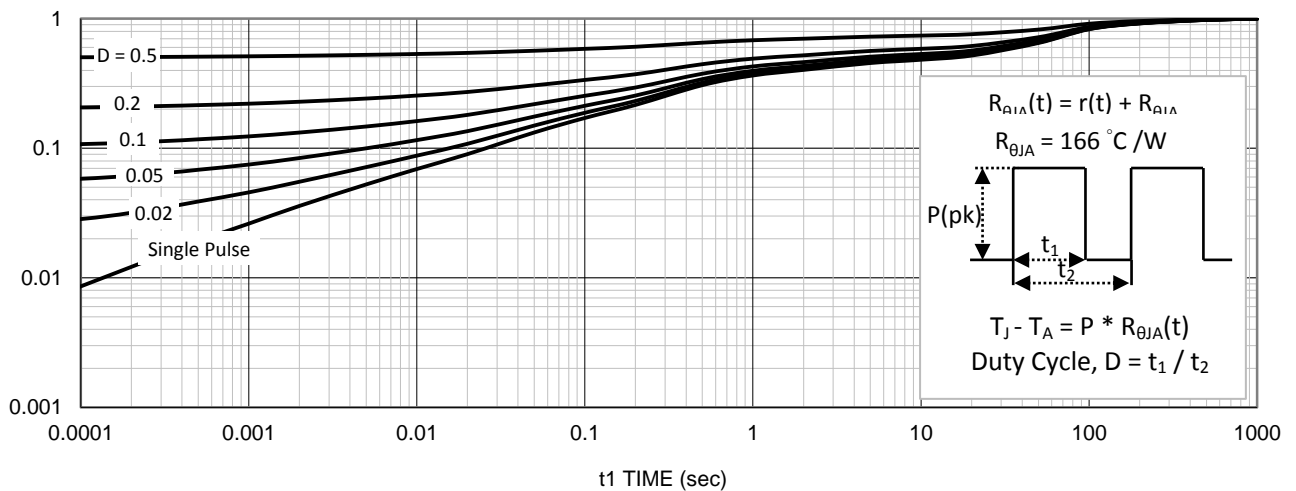
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient